

# Sanna Ranta

## List of Publications by Year in Descending Order

**Source:** <https://exaly.com/author-pdf/367923/sanna-ranta-publications-by-year.pdf>

**Version:** 2024-04-28

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

30  
papers

363  
citations

11  
h-index

18  
g-index

43  
ext. papers

503  
ext. citations

2.5  
avg, IF

3.16  
L-index

#	Paper	IF	Citations
30	Thermal behavior and power scaling potential of membrane external-cavity surface-emitting lasers (MECSELs). <i>IEEE Journal of Quantum Electronics</i> , <b>2022</b> , 1-1	2	1
29	Watt-level blue light for precision spectroscopy, laser cooling and trapping of strontium and cadmium atoms. <i>Optics Express</i> , <b>2021</b> , 29, 25462-25476	3.3	2
28	GaAs surface passivation for InAs/GaAs quantum dot based nanophotonic devices. <i>Nanotechnology</i> , <b>2021</b> , 32, 130001	3.4	2
27	InGaN-diode-pumped AlGaInP VECSEL with sub-kHz linewidth at 689 nm. <i>Optics Express</i> , <b>2021</b> , 29, 3258-3268	3.5	1
26	Power scaling and thermal lensing in 825 nm emitting membrane external-cavity surface-emitting lasers. <i>Optics Letters</i> , <b>2020</b> , 45, 547	3	8
25	Thin-film InAs/GaAs quantum dot solar cell with planar and pyramidal back reflectors. <i>Applied Optics</i> , <b>2020</b> , 59, 6304-6308	1.7	2
24	Thermophotonic cooling in GaAs based light emitters. <i>Applied Physics Letters</i> , <b>2019</b> , 114, 051101	3.4	11
23	AlGaAs/AlGaInP VECSELs With Direct Emission at 740-770 nm. <i>IEEE Photonics Technology Letters</i> , <b>2019</b> , 31, 1245-1248	2.2	8
22	Comparison of single-side and double-side pumping of membrane external-cavity surface-emitting lasers. <i>Optics Letters</i> , <b>2019</b> , 44, 1146-1149	3	10
21	Narrow-Linewidth 780-nm DFB Lasers Fabricated Using Nanoimprint Lithography. <i>IEEE Photonics Technology Letters</i> , <b>2018</b> , 30, 51-54	2.2	11
20	AlGaAs-based vertical-external-cavity surface-emitting laser exceeding 4 W of direct emission power in the 740-790 nm spectral range. <i>Optics Letters</i> , <b>2018</b> , 43, 1578-1581	3	8
19	72-W vertical-external-cavity surface-emitting laser with 1180-nm emission for laser guide star adaptive optics. <i>Electronics Letters</i> , <b>2018</b> , 54, 1135-1137	1.1	8
18	Distributed feedback lasers with alternating laterally coupled ridge-waveguide surface gratings. <i>Optics Letters</i> , <b>2017</b> , 42, 3141-3144	3	3
17	A 1.5-W frequency doubled semiconductor disk laser tunable over 40 nm at around 745 nm <b>2016</b> ,		2
16	1180nm VECSEL with 50 W output power <b>2015</b> ,		4
15	750 nm 1.5 W frequency-doubled semiconductor disk laser with a 44 nm tuning range. <i>Optics Letters</i> , <b>2015</b> , 40, 4380-3	3	11
14	Pulsed high-power yellow-orange VECSEL <b>2014</b> ,		1

13	High-efficiency 20 W yellow VECSEL. <i>Optics Express</i> , <b>2014</b> , 22, 6372-80	3.3	60
12	Optically Pumped Semiconductor Lasers for Precision Spectroscopic Applications. <i>IEEE Journal of Quantum Electronics</i> , <b>2013</b> , 49, 719-727	2	12
11	1180nm VECSEL with output power beyond 20 W. <i>Electronics Letters</i> , <b>2013</b> , 49, 59-60	1.1	21
10	High power (23W) vertical external cavity surface emitting laser emitting at 1180 nm <b>2013</b> ,		4
9	Mode-locked VECSEL emitting 5 ps pulses at 675 nm. <i>Optics Letters</i> , <b>2013</b> , 38, 2289-91	3	25
8	Narrow linewidth 1118/559 nm VECSEL based on strain compensated GaInAs/GaAs quantum-wells for laser cooling of Mg-ions. <i>Optical Materials Express</i> , <b>2012</b> , 2, 1011	2.6	13
7	Femtosecond mode-locked holmium fiber laser pumped by semiconductor disk laser. <i>Optics Letters</i> , <b>2012</b> , 37, 1448-50	3	42
6	Strain compensated 1120nm GaInAs/GaAs vertical external-cavity surface-emitting laser grown by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2011</b> , 335, 4-9	1.6	8
5	High-Power 1.48- $\mu\text{m}$ Wafer-Fused Optically Pumped Semiconductor Disk Laser. <i>IEEE Photonics Technology Letters</i> , <b>2011</b> , 23, 917-919	2.2	18
4	Asymmetric waveguide laser diode operated in gain switching mode with high-power optical pulse generation. <i>Electronics Letters</i> , <b>2010</b> , 46, 65	1.1	19
3	Raman fiber laser pumped by a semiconductor disk laser and mode locked by a semiconductor saturable absorber mirror. <i>Optics Letters</i> , <b>2010</b> , 35, 3529-31	3	31
2	Laterally-corrugated ridge-waveguide distributed feedback lasers at 980 nm. <i>Optical and Quantum Electronics</i> , <b>2009</b> , 41, 11-16	2.4	2
1	Dual-wavelength generation by vertical external cavity surface-emitting laser. <i>Optics Express</i> , <b>2007</b> , 15, 13451-6	3.3	14